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| 08:00 - 09:00 | Registration | |
| 09:00 - 10:20 | <p>Session I</p> <p>-</p> <p>Opening Session</p> <p>chair : C. Fager / co-chair : T.M. Guerrero</p> | <p>Welcome Address : Conference Chairs</p> <p>Keynote Talk : Dominique Baillargeat</p> <p>Overview of the Xlim Lab</p> <p>Keynote Talk : Greg Baker</p> <p>Future Challenges in High Power Technologies for Microwave and Millimeter-Wave Applications</p> |
| 10:20 - 10:40 | Coffee Break | Poster Session I |
| 10:40 - 12:40 | <p>Session II - Trap GaN Modeling</p> <p>chair : E. Limiti / co-chair : A. Martin</p> <p><u>Keynote Talk</u>: S. Piotrovitch, Overview of GaN Technologies at III-V Lab & UMS addressing Microwave and Millimeter-Wave Applications</p> <p>S. Fakhfakh : On-wafer Time-Domain and Low-Frequency Measurements of GaN HEMTs for Accurate Trap Modeling and its Impact on Pulse-to-Pulse Stability,</p> <p>J. Gomes : Deep-Level Traps' Capture Time Constant and its Impact on Nonlinear GaN HEMT Modeling,</p> <p>K. Kikuchi : Comparison of GaN HEMT Technology Processes by Large-Signal Low-Frequency Measurements</p> <p>M. Bouslama : Low Frequency Drain Noise Characterization of Different Technologies of GaN HEMTs: Investigation of Trapping Mechanism,</p> | |
| 12:40 - 14:00 | Lunch Break | Poster Session I |
| 14:00 - 16:00 | <p>Session III - Design Strategies for Power Amplifiers</p> <p>chair : R. Quaglia / co-chair : M. Campovecchio</p> <p><u>Keynote Talk</u>: N. DasGupta, GaN-based HEMTs for RF Power Applications</p> <p>R. Giofrè, A Q-Band MMIC Power Amplifier in GaN on Si Technology for Space Applications,</p> <p>C. Potier, Design of MMIC power amplifier designs based on InAlGaN/GaN HEMT technology in Ka band</p> <p>M. Montaseri, Performance Improvement of Multi-Stacked CMOS mm-Wave Power Amplifiers Based on Negative Capacitance Phase Compensation,</p> <p>G. Lasser, Independent Dynamic Gate Bias for a Two-Stage Amplifier for Amplitude and Phase Linearization,</p> | |
| 16:00 - 16:20 | Coffee Break | Poster Session I |
| 16:20 - 18:20 | <p>Session IV - Advanced Measurement Techniques</p> <p>chair : T. Reveyrand / co-chair : G. Neveux</p> <p><u>Industrial Talk</u>: National Instruments</p> <p>Malcolm Edwards, Module Design: The case for EDA integration</p> <p>V. Gillet, An Unequally Spaced Multi-Tone Passive Load-Pull (USMT-PLP) to simultaneously characterize Linearity and Efficiency of RF Power Devices,</p> <p>J. Martens, Quasi-linear Microwave Measurements for Optoelectronic Systems Analysis,</p> <p>W. Aouimeur, A Fully In-Situ Reflectometer in G band in 55 nm SiGe BiCMOS</p> <p>A. Petrocchi, An Ultra-Wideband Setup to Monitor Antenna-Impedance Variations in Low-Cost IoT Transmitters</p> | |
| 18:20 - 18:30 | Break | |
| 18:30 - 19:20 | NVNA Users' forum | |
| | <p>T. Gasseling, A Robust and Reliable Behavioral Model of High Power GaN HEMTs for RF Doherty Amplifier Application</p> <p>T. Reveyrand, Unknown Thru Calibration Algorithm</p> | |
| 19:45 | Gala Dinner | |